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Extreme Ultraviolet (EUV) Lithography X

Kenneth A. Goldberg
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Contents

vii *Authors*
xi *Conference Committee*

THE FUTURE IS HIGH NA

- 10957 08 **Overview and status of the 0.5NA EUV microfield exposure tool at Berkeley Lab (Invited Paper)** [10957-4]
10957 09 **High NA EUV lithography: next step in EUV imaging** [10957-5]

INORGANIC RESISTS: JOINT SESSION WITH CONFERENCES 10960 AND 10957

- 10957 0B **The role of the organic shell in hybrid molecular materials for EUV lithography** [10957-7]
10957 0D **Zinc-based metal oxoclusters: towards enhanced EUV absorptivity** [10957-9]

STOCHASTICS AND EXPOSURE MECHANISMS: JOINT SESSION WITH CONFERENCES 10960 AND 10957

- 10957 0E **Stochastic printing failures in EUV lithography (Invited Paper)** [10957-10]
10957 0F **Fundamentals of resist stochastics effect for single-expose EUV patterning** [10957-11]

ORDER FROM CHAOS: STOCHASTIC MODELING

- 10957 0G **Impact of asymmetrically localized and cascading secondary electron generation on stochastic defects in EUV lithography** [10957-12]
10957 0H **Impact of local variability on defect-aware process windows (Invited Paper)** [10957-13]
10957 0I **Unraveling the EUV photoresist reactions: which, how much, and how do they relate to printing performance (Invited Paper)** [10957-14]
10957 0J **OPC strategies to reduce failure rates with rigorous resist model stochastic simulations in EUVL** [10957-15]

EUV MASK FIDELITY

- 10957 OK **Towards ultimate image placement accuracy for EUV mask writing with pattern shift process** [10957-16]
- 10957 OL **EUV mask challenges and requirements for ultimate single exposure interconnects (Invited Paper)** [10957-17]
- 10957 OM **Influence of mask line width roughness on programmed pattern defect printability** [10957-18]
- 10957 ON **Impact of EUV absorber variations on wafer patterning** [10957-19]
- 10957 OO **Ion beam etching of new absorber materials for sub-5nm EUV masks** [10957-20]

PRINTING AT THE EDGE: EUV PATTERNING APPLICATIONS

- 10957 OR **LCDU optimization of STT-MRAM 50nm pitch MTJ pillars for process window improvement** [10957-22]
- 10957 OS **Impact of sequential infiltration synthesis (SIS) on roughness and stochastic nano-failures for EUVL patterning** [10957-23]

EUV PATTERNING AND ETCH: JOINT SESSION WITH CONFERENCES 10957 AND 10963

- 10957 OT **Staggered pillar patterning using 0.33NA EUV lithography** [10957-25]

EUV MASKS, DEFECTS, AND PELLICLES

- 10957 OU **Advanced particle contamination control in EUV scanners** [10957-27]
- 10957 OV **Upgrade to the SHARP EUV mask microscope** [10957-28]
- 10957 OW **Absorber and phase defect inspection on EUV reticles using RESCAN** [10957-29]

EUV IMAGING ENHANCEMENT I

- 10957 OZ **3D mask effects in high NA EUV imaging** [10957-32]
- 10957 10 **Investigation of mask absorber induced image shift in EUV lithography (Invited Paper)** [10957-33]

10957 12 **Implementation of different cost functions for EUV mask optimization for next generation beyond 7 nm** [10957-35]

EUV IMAGING ENHANCEMENT II

10957 13 **Compatibility assessment of novel reticle absorber materials for use in EUV lithography systems** [10957-36]

10957 15 **Advanced multilayer mirror design to mitigate EUV shadowing** [10957-38]

EUV OPC AND MODELING: JOINT SESSION WITH CONFERENCES 10957 AND 10962

10957 1C **Mask 3D effect reduction and defect printability of etched multilayer EUV mask** [10957-46]

10957 1D **Development of fast rigorous simulator for large-area EUV lithography simulation** [10957-45]

POSTER SESSION

10957 1G **Actinic inband EUV reflectometry AIMER compared to ALS blank qualification and applied to structured masks** [10957-47]

10957 1I **High-precision MoSi multilayer coatings at high-volume for continued EUVL infrastructure development** [10957-49]

10957 1J **The defect mitigation on EUV stack by track based technology** [10957-50]

10957 1K **EUV-LET 2.0: a compact exposure tool for industrial research at a wavelength of 13.5 nm** [10957-51]

10957 1L **Photon detector calibration in the EUV spectral range at PTB** [10957-52]

10957 1N **Line-edge roughness on fin-field-effect-transistor performance for below 10nm patterns** [10957-54]

10957 1O **Calibrated PSCAR stochastic simulation** [10957-56]

10957 1P **Novel technologies in coater/developer to enhance the CD stability and to improve the defectivity toward N7 and smaller nodes** [10957-57]

10957 1Q **Simulation of statistical effects in exposure and development of EUV photoresists using the percolation and diffusion limited aggregation model** [10957-58]

- 10957 1S **Update of the development progress of the high power LPP-EUV light source using a magnetic field** [10957-61]
- 10957 1X **Achieving diffraction-limited performance on the Berkeley MET5** [10957-67]

Authors

Numbers in the index correspond to the last two digits of the seven-digit citation identifier (CID) article numbering system used in Proceedings of SPIE. The first five digits reflect the volume number. Base 36 numbering is employed for the last two digits and indicates the order of articles within the volume. Numbers start with 00, 01, 02, 03, 04, 05, 06, 07, 08, 09, 0A, 0B...0Z, followed by 10-1Z, 20-2Z, etc.

Abe, Tamotsu, 1S
Akiteru, Ko, 1J
Allezy, Arnaud, 08
Anderson, Christopher, 08, 1X
Arps, J., 1G
Babalik, A., 1L
Babuschkin, A., 1L
Bahrenberg, Lukas, 1K
Banine, Vadim, 0U
Barboutis, A., 1L
Barouch, Eytan, 1D
Bekaert, Joost, 0H
Bender, Markus, 0K
Benk, Markus, 0V
Biafore, John J., 0J
Biermanns-Föth, A., 1G
Biesemans, Serge, 1O
Bilski, Bartosz, 09
Blanc, Romuald, 0T
Blanco, Victor, 0S
Blankenship, David, 0J
Bonam, Ravi, 0L
Bottiglieri, Gerardo, 09, 0Z
Brose, Sascha, 1K
Buchholz, C., 1L
Burkhardt, Martin, 10
Cantrell, G. R., 0K
Carcasi, Michael, 1O
Castellanos, Sonia, 0B, 0D
Cerbu, Dorin, 0H
Cerio, Frank, 0O
Chao, Weilun, 08, 0V, 1X
Charley, Anne-Laure, 0T
Choi, Yohan, 0L
Church, Jennifer, 10
Cloin, Christian, 0U
Cork, Carl, 08, 1X
Cork, Will, 08
Corliss, Daniel, 0L
Crotti, Davide, 0R
Danylyuk, Serhiy, 1K
De Bisschop, Peter, 0E, 0I, 1O
Dejkameh, Atoosa, 0W
Delano, Rene, 08
Demand, Marc, 1P
DePonte, Jason, 08
de Poortere, Etienne, 0S
de Roest, David, 0S
de Rooij-Lohmann, Veronique, 13
De Silva, Anuja, 0F, 10
De Simone, Danilo, 0I, 0R, 0S, 0T, 1O
Devasahayam, Adrian J., 0O
Dickinson, Michael, 08, 1X
Dinh, Cong Que, 1O
Dunn, Derren, 0L
Ekinci, Yasin, 0B, 0D, 0W
Enomoto, Masashi, 1P
Ercken, Monique, 0R
Erdmann, Andreas, 0Z
Evanschitzky, Peter, 0Z
Fallica, Roberto, 0T
Felix, Nelson M., 0F, 0L, 10, 1J
Fernandez, Sara, 0W
Finken, Michael, 0K
Fischer, A., 1L
Fliervoet, Timon, 09, 0Z
Foubert, Philippe, 1O, 1P
Frommhold, Andreas, 0H, 0N
Fühner, Tim, 0N
Fukuda, Hiroshi, 0G
Gaines, Geoff, 08, 1X
Gallagher, Emily, 0N
Gamsby, Jeff, 08, 1X
Goldberg, Kenneth, 0V
Goldfarb, Dario L., 0F
Graeupner, Paul, 09
Graves, Trey, 0J
Green, Michael, 0L
Gullikson, Eric, 08
Halder, Sandip, 0R
Ham, Young, 0L
Hara, Arisa, 0H
Hayashi, Hideyuki, 1S
Helfenstein, Patrick, 0W
Hendrickx, Eric, 0E, 0H, 0S
Hetzer, Dave, 1J
Hody, Hubert, 0R
Hori, Tsukasa, 1S
Hsu, Stephen, 09
Hubbard, Alex, 1J
Huli, Lior, 1J
Ide, Hiroyuki, 1O
Iida, Susumu, 1C
Ip, Vincent, 0O
Jaroslawzew, S., 1L
Jayaram, Srividya, 12
Jiang, Fan, 12
Jones, Gideon, 08, 1X

Juschkin, Larissa, 1K
Kai, Akiko, 1J
Kamberian, Henry, 0L
Kamei, Yuya, 1O, 1P
Kamo, Takashi, 0M, 1C
Kandel, Yudhishthir, 0N
Kasprowicz, Bryan, 0L
Kawakami, Shinichiro, 1J, 1P
Kazazis, Dimitrios, 0W
Kim, Sang-Kon, 1N
Kissoon, Nicola, 0S
Kodama, Takeshi, 1S
Kohli, Sandeep, 0O
Kondo, Yoshihiro, 1O
Kriese, Michael, 1I
Laubis, C., 1L
Lazzarino, Frederic, 0S, 0T
Lebert, Rainer, 1G, 1K
Lee, Jungkyung, 0T
Lee, Kilyoung, 0T
Lee, Meng H., 0O
Lee, Patrick, 0J
Lehnert, J., 1L
Lemley, Corey, 1J
Lercel, Michael, 0U
Li, Yang, 1I
Lim, Chang-Moon, 0T
Locans, Uldis, 0W
Loosen, Peter, 1K
Lorusso, Gian, 0T
Magoshi, Shunko, 1C
Mao, Ming, 0S
Maslow, Mark John, 0H
Mc Manus, Moyra, 0S
McNamara, John, 09
Meli, Luciana, 0F, 0L, 10, 1J
Meliorisz, Balint, 1O
Melvin, Lawrence S., III, 0N
Mentzel, H., 1L
Meyers, Stephen, 08
Minekawa, Yukie, 1O
Missalla, T., 1G
Miyakawa, Ryan, 08, 0V, 1X
Miyao, Kenichi, 1S
Miyata, Yuichiro, 1J
Mizoguchi, Hakaru, 1S
Mochi, Iacopo, 0W
Morikawa, Yasutaka, 0M, 1C
Moriya, Teruhiko, 1O
Muramatsu, Makoto, 1P
Murray, Cody, 1J
Nafus, Kathleen, 1O, 1P
Nagahara, Seiji, 1O
Nagai, Shinji, 1S
Nakarai, Hiroaki, 1S
Naulleau, Patrick, 08, 0V, 15, 1X
Nebling, Ricarda, 0W
Neureuther, Andrew, 1S
Nikipelov, Andrey, 0U
Oh, Sharon, 1X

Oikawa, Noriaki, 0H
Okamoto, Takeshi, 1S
Pak, Murat, 0R
Park, Chan-Ha, 0T
Park, Sarohan, 0T
Pathak, Abhinav, 0H, 0S
Petersen, John S., 0I, 1O
Petrillo, Karen, 1J
Phiesel, C., 1G
Piel, C., 1G
Piumi, Daniele, 0S
Platonov, Yuriy, 1I
Pollentier, Ivan, 0I
Progler, Chris, 0L
Proske, Stefan, 0K
Puls, J., 1L
Rajeev, Rajendran, 0W
Ramadan, Mohamed, 0L
Rassoul, Nouredine, 0T
Rekawa, Seno, 08, 1X
Rincon Delgadillo, Paulina, 0S
Rispen, Gijbert, 0H, 0S
Robertson, Stewart A., 0J
Robinson, Chris, 10
Roesch, Matthias, 09
Ronse, Kurt, 0T
Rook, Katrina, 0O
Saito, Takashi, 1S
Salmassi, Farhad, 08
Sankar Kar, Gouri, 0R
Sano, Yohei, 1P
Sasaki, Akira, 1Q
Schiffelers, Guido, 0H, 0S
Scholze, F., 1L
Schönstedt, A., 1L
Sherwin, Stuart, 15
Shibata, Naoki, 1J
Shimada, Ryo, 1O
Shiozawa, Takahiro, 1J
Shiraishi, Gousuke, 1O
Shiraishi, Yutaka, 1S
Shusuke, Yoshitake, 0N
Sidorkin, Vadim, 0K
Sintschuk, M., 1L
Slachter, Bram, 0H
Smeets, Christophe, 0U
Sonoda, Akihiro, 1J, 1P
Souriau, Laurent, 0R
Srinivasan, Narasimhan, 0O
Stadelhoff, C., 1L
Steele, Jeffery, 1I
Stock, Hans-Jürgen, 1O
Stollenwerk, Jochen, 1K
Storm, Arnold, 13
Stortelder, Jetske, 13
Sun, Yuyang, 12
Tadokoro, Masahide, 1P
Tagbo, C., 1L
Takeshita, Kazuhiro, 1O
Tamaddon, Amir-Hossein, 0T

Tanaka, Satoshi, 1C
Thakur, Neha, 0D
Tomczak, Yoann, 0S
Tomono, Masaru, 1O
Tritchkov, Alexander, 12
Troost, Kars, 09
Tseng, Li-Ting, 0W
Uchiyama, Takayuki, 1C
Ueda, Atsushi, 1S
Ueda, Kenichi, 1J
Vaglio Pret, Alessandro, 0J
van de Kerkhof, Mark, 0U
Van de Kerkhove, Jeroen, 0T
Vandenbergh, Geert, 0I, 0S, 0T, 1O
Vandenbroeck, Nadia, 0T
van de Wetering, Ferdi, 0U
Vanelder, Pieter, 0R, 0S, 0T
van Empel, Tjarko, 0U
Van Look, Lieve, 0T
Van Roey, Frieda, 0T
van Schaik, Willem, 13
van Schoot, Jan, 09
van Setten, Eelco, 09, 0Z
Vockenhuber, Michaela, 0B, 0D
Vollmer, Brandon, 08
Wada, Toshiharu, 1J
Wahlisch, Felix, 0H
Waller, Laura, 15
Watanabe, Yukio, 1S
Wei, Alex, 12
Welling, Ulrich, 0N
Word, James, 12
Wu, Chien-Ching, 13
Wu, Lianjia, 0B
Yaegashi, Hidetami, 0H
Yakunin, Andrei, 0U
Yamane, Takeshi, 0M, 1C
Yamauchi, Takashi, 1P
Yanagida, Tatsuya, 1S
Yano, Hidetsugu, 1J
Yasin, Farukh, 0R
Yeung, Michael, 1D
Yoon, So-Won, 1N
Yoshida, Keisuke, 0H
Yoshida, Yuichi, 1O
Yoshihara, Kosuke, 1O
Zehm, Daniel, 08
Zekry, Joseph, 09
Zhang, Xima, 12
Zhu, Wenhua, 08, 1X
Zimmermann, Joerg, 09
Zimmermann, Stephan, 0K

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Session Chairs

- 1 Keynote Session
Kenneth A. Goldberg, Lawrence Berkeley National Laboratory
(United States)
Nelson M. Felix, IBM Corporation (United States)
- 2 The Future is High NA
Patrick P. Naulleau, Lawrence Berkeley National Laboratory
(United States)
Jos P. Benschop, ASML Netherlands B.V. (Netherlands)
- 3 Inorganic Resists: Joint session with conferences 10960 and 10957
Robert L. Brainard, SUNY CNSE/SUNYIT (United States)
Jason K. Stowers, Inpria Corporation (United States)
- 4 Stochastics and Exposure Mechanisms: Joint session with
conferences 10960 and 10957
Florian Gstrein, Intel Corporation (United States)
Thomas I. Wallow, ASML Brion (United States)
- 5 Order from Chaos: Stochastic Modeling
Sonia Castellanos Ortega, Advanced Research Center for
Nanolithography (Netherlands)
Shinji Okazaki, ALITECS Company, Ltd. (Japan)
- 6 EUV Mask Fidelity
Martin Burkhardt, IBM Thomas J. Watson Research Center
(United States)
Bryan S. Kasprovicz, Photronics, Inc. (United States)

- 7 Printing at the Edge: EUV Patterning Applications
Christopher S. Ngai, Applied Materials, Inc. (United States)
Luciana Meli, IBM Corporation (United States)
- 8 EUV Patterning and Etch: Joint session with conferences 10957 and 10963
Rich S. Wise, Lam Research Corporation (United States)
Anna Lio, Intel Corporation (United States)
- 9 EUV Masks, Defects, and Pellicles
Emily E. Gallagher, IMEC (Belgium)
Moshe E. Preil, KLA-Tencor Corporation (United States)
- 10 EUV Imaging Enhancement I
Andreas Erdmann, Fraunhofer-Institut für Integrierte Systeme und Bauelementetechnologie IISB (Germany)
Eric Hendrickx, IMEC (Belgium)
- 11 EUV Imaging Enhancement II
Naoya Hayashi, Dai Nippon Printing Company, Ltd. (Japan)
Kurt G. Ronse, IMEC (Belgium)
- 12 Progress in EUV Sources
Akiyoshi Suzuki, Gigaphoton Inc. (Japan)
Anna Lio, Intel Corporation (United States)
- 13 EUV OPC and Modeling: Joint session with conferences 10957 and 10962
Kevin Lucas, Synopsys, Inc. (United States)
Soichi Inoue, Toshiba Corporation (Japan)

